



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



SOT23 PNP SILICON PLANAR MEDIUM POWER TRANSISTORS

FMMTA56

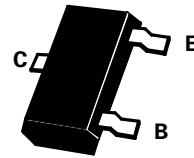
ISSUE 4 – MARCH 2001



FEATURES

* Gain of 50 at $I_C=100\text{mA}$

PARTMARKING DETAIL - FMMTA56 - 2G
FMMTA56R - MB



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FMMTA56	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-4	V
Continuous Collector Current	I_C	-500	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

PARAMETER	SYMBOL	FMMTA56		UNIT	CONDITIONS.
		MIN.	MAX.		
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80		V	$I_C=-1\text{mA}, I_B=0^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-4		V	$I_E=-100\mu\text{A}, I_C=0$
Collector-Emitter Cut-Off Current	I_{CES}		-0.1	μA	$V_{CE}=-60\text{V}$
Collector-Base Cut-Off Current	I_{CBO}		-0.1	μA	$V_{CB}=-80\text{V}, I_E=0$ $V_{CB}=-60\text{V}, I_E=0$
Static Forward Current Transfer Ratio	h_{FE}	50 50			$I_C=-10\text{mA}, V_{CE}=1\text{V}^*$ $I_C=-100\text{mA}, V_{CE}=1\text{V}^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-0.25	V	$I_C=-100\text{mA}, I_B=-10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-1.2	V	$I_C=-100\text{mA}, V_{CE}=-1\text{V}^*$
Transition Frequency	f_T	100		MHz	$I_C=-10\text{mA}, V_{CE}=-2\text{V}$ $f=100\text{MHz}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

